

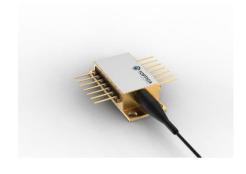
Revision 0.50

2025-05-13

### SINGLE FREQUENCY LASER External Cavity Diode Laser



General Product Information	
Product	Application
770 nm mini-ECL	Spectroscopy (K D1 line)
with hermetic 14-Pin Butterfly Housing (RoHS compliant)	Metrology
including Monitor Diode, Thermoelectric Cooler and Thermistor	Quantum Technology
with integrated μ-Isolator and PM Fiber	



#### Absolute Maximum Ratings Parameter Symbol Unit min typ max °C Storage Temperature $\mathsf{T}_\mathsf{S}$ -40 85 Operational Temperature at Case °C -40 85 $\mathsf{T}_\mathsf{C}$ Operational Temperature at Chip T<sub>chip</sub> °C 50 200 Forward Current $\mathsf{I}_\mathsf{F}$ mΑ Reverse Voltage ٧ 2 $V_{\mathsf{R}}$ Output Power Popt mW 25 TEC Current Α 1.8 $\mathsf{I}_{\mathsf{TEC}}$ TEC Voltage $V_{\text{TEC}} \\$ ٧ 3.2

Measurement Conditions / Comments Stress in excess of one of the Absolute Maximum Ratings may damage the laser. Please note that a damaging optical power level may occur although the maximum current is not reached. These are stress ratings only, and functional operation at these or any other conditions beyond those indicated under Recommended Operational Conditions is not implied.

Recommended Operational Conditions					
Parameter	Symbol	Unit	min	typ	max
Operational Temperature at Case	T <sub>case</sub>	°C	-20		65
Operational Temperature at Chip	$T_{chip}$	°C	0		45
Forward Current	I <sub>F</sub>	mA			180
Output Power	P <sub>opt</sub>	mW	5		18

Measurement Conditions / Comments
measured by integrated Thermistor



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Characteristics	Tchip = 25 °C at BC	DL				
Parameter	Symbol	Unit	min	typ	max	Measurement Conditions / Comments
Center Wavelength	$\lambda_{\text{C}}$	nm	769	770	771	
Target Wavelength	$\lambda_{\mathrm{T}}$	nm		770.11		reached within Tchip = 0 °C 45 °C
Linewidth	$\Delta\lambda$	MHz		0.1	0.3	measured in the time scale of 1 ms
Mode-hop free Tuning Range	$\Delta \lambda_{tune}$	pm		15		By current tuning, at target wavelength
Output Power	P <sub>opt</sub>	mW			18	
Sidemode Suppression Ratio	SMSR	dB	30	45		Popt = 18 mW
Temp. Coefficient of Wavelength	dλ/dT	nm/K		0.008		
Current Coefficient of Wavelength	dλ / dl	nm/mA		0.001		
Laser Current	$I_{LD}$	mA			180	
Slope Efficiency	η	mW/mA		0.2		
Threshold Current	I <sub>th</sub>	mA		60		
Polarization Extinction Ratio	PER	dB		20		Popt = 25 mW
Monitor Diode						
Parameter	Symbol	Unit	min	typ	max	Measurement Conditions / Comments
Monitor Detector Responsivity	I <sub>mon</sub> / P <sub>op</sub>	μA/mW		10		5 V

Thermoelectric Cooler					
Parameter	Symbol	Unit	min	typ	max
Current	I <sub>TEC</sub>	А		0.4	
Voltage	$U_TEC$	V		1.5	
Power Dissipation (total loss at case)	P <sub>loss</sub>	W		0.5	
Temperature Difference	ΔΤ	K			50

Measurement Conditions / Comments
Popt = 18 mW, ΔT = 20 K
Popt = 18 mW, ΔT = 20 K
Popt = 18 mW, ΔT = 20 K
Popt = 18 mW, ΔT =  Tcase - Tchip

Thermistor (Standard NTC Type)					
Parameter	Symbol	Unit	min	typ	max
Resistance	R	kΩ		10	
Beta Coefficient	b			3892	
Steinhart & Hart Coefficient A	А		1.	1293 x 10	-3
Steinhart & Hart Coefficient B	В		2.	3410 x 10 <sup>-</sup>	-4
Steinhart & Hart Coefficient C	С		8.	7755 x 10	-8

Measurement Conditions / Comments
Tchip = 25 °C
$R_1/R_2 = e^{\beta(1/T_1 - 1/T_2)}$ at Tchip = 0 50 °C
$1/T = A + B(\ln R) + C(\ln R)^3$
T: Temperature in Kelvin
R: resistance at T in $\Omega$

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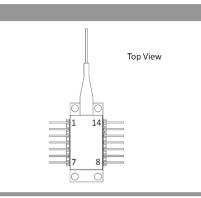
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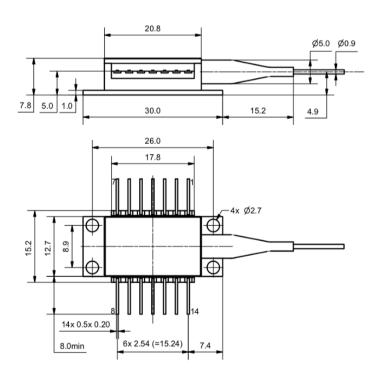
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Pi	n As	ssignment		
	1	Thermoelectric Cooler (+)	14	Thermoelectric Cooler (-)
	2	Thermistor	13	Case
	3	Photo Diode Anode	12	not connected
	4	Photo Diode Cathode	11	Laser Diode Cathode
	5	Thermistor	10	Laser Diode Anode
	6	not connected	9	not connected
	7	not connected	8	not connected



### Package Drawings





\* For properties of fiber pigtail and connector type please see P/N specification sheet

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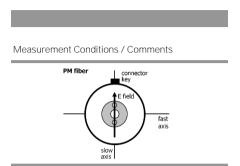
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## SINGLE FREQUENCY LASER External Cavity Diode Laser



Parameter						
900 / 125 / 5.5 μm, UV/Polyester-elastomer Coating (I = 1 +/-0.1 m)						
FC/APC (narrow key / 2mm)						



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## SINGLE FREQUENCY LASER External Cavity Diode Laser



#### Unpacking, Installation and Laser Safety

contribute to a long lifetime of the diode.

Unpacking the laser diodes should only be done at electrostatic safe workstations (EPA). Though protection against electro static discharge (ESD) is implemented in the laser package, charges may occur at surfaces. Please store this product in its original package at a dry, clean place until final use. During device installation, ESD protection has to be maintained.





A laser diode is sensitive against optical feedback, so an optical isolator may be required in order to avoid any disturbance of the emission spectrum. Operating at moderate temperatures on proper heat sinks will



INVISIBLE LASER RADIATION
AVOID EYE OR SKIN EXPOSUR
TO DIRECT OR SCATTERED RADIATION
CLASS 4 LASER PRODUCT
WAVELENGTH 770 nm
MAX. OUTPUT POWER 30 mW

IEC-60825-1

Avoid direct and/or indirect exposure to the free running beam. Collimating and focussing the free running beam with optics as common in optical instruments will increase threat to the human eye.

Each laser diode will come with an individual test protocol verifying the parameters given in this document.





Performance figures, data and any illustrative material provided in this specification are typical and must be specifically confirmed in writing by eagleyard Photonics before they become applicable to any particular order or contract. In accordance with the eagleyard Photonics policy of continuous improvement specifications may change without notice.



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